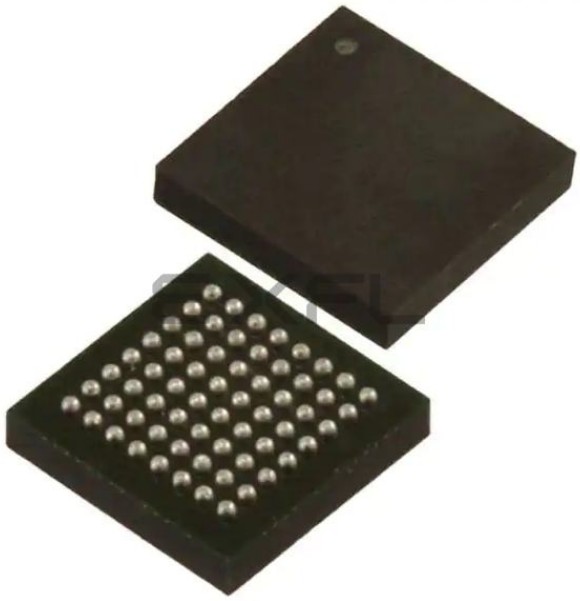
Lattice Semiconductor Corporation - LCMXO2-256HC-5UMG64I Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

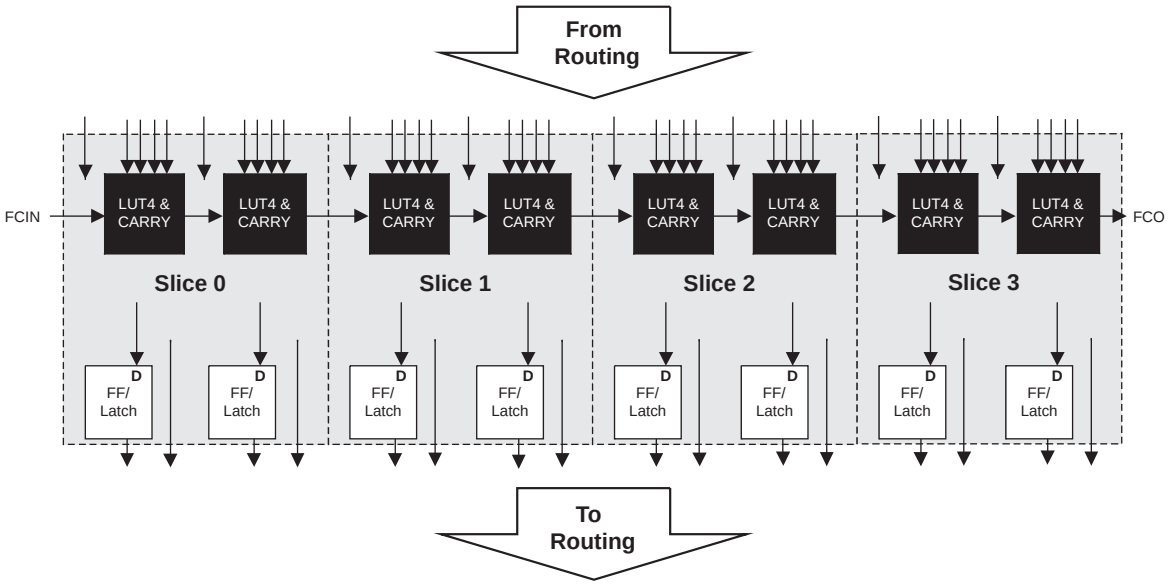
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	32
Number of Logic Elements/Cells	256
Total RAM Bits	-
Number of I/O	44
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	64-VFBGA
Supplier Device Package	64-UCBGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-256hc-5umg64i

Figure 2-3. PFU Block Diagram



Slices

Slices 0-3 contain two LUT4s feeding two registers. Slices 0-2 can be configured as distributed memory. Table 2-1 shows the capability of the slices in PFU blocks along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. The control logic performs set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2-1. Resources and Modes Available per Slice

Slice	PFU Block	
	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 1	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 2	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2-4 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks. All slices have 15 inputs from routing and one from the carry-chain (from the adjacent slice or PFU). There are seven outputs: six for routing and one to carry-chain (to the adjacent PFU). Table 2-2 lists the signals associated with Slices 0-3.

This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the t_{LOCK} parameter has been satisfied.

The MachXO2 also has a feature that allows the user to select between two different reference clock sources dynamically. This feature is implemented using the PLLREFCS primitive. The timing parameters for the PLL are shown in the sysCLOCK PLL Timing table.

The MachXO2 PLL contains a WISHBONE port feature that allows the PLL settings, including divider values, to be dynamically changed from the user logic. When using this feature the EFB block must also be instantiated in the design to allow access to the WISHBONE ports. Similar to the dynamic phase adjustment, when PLL settings are updated through the WISHBONE port the PLL may lose lock and not relock until the t_{LOCK} parameter has been satisfied. The timing parameters for the PLL are shown in the sysCLOCK PLL Timing table.

For more details on the PLL and the WISHBONE interface, see TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide.

Figure 2-7. PLL Diagram

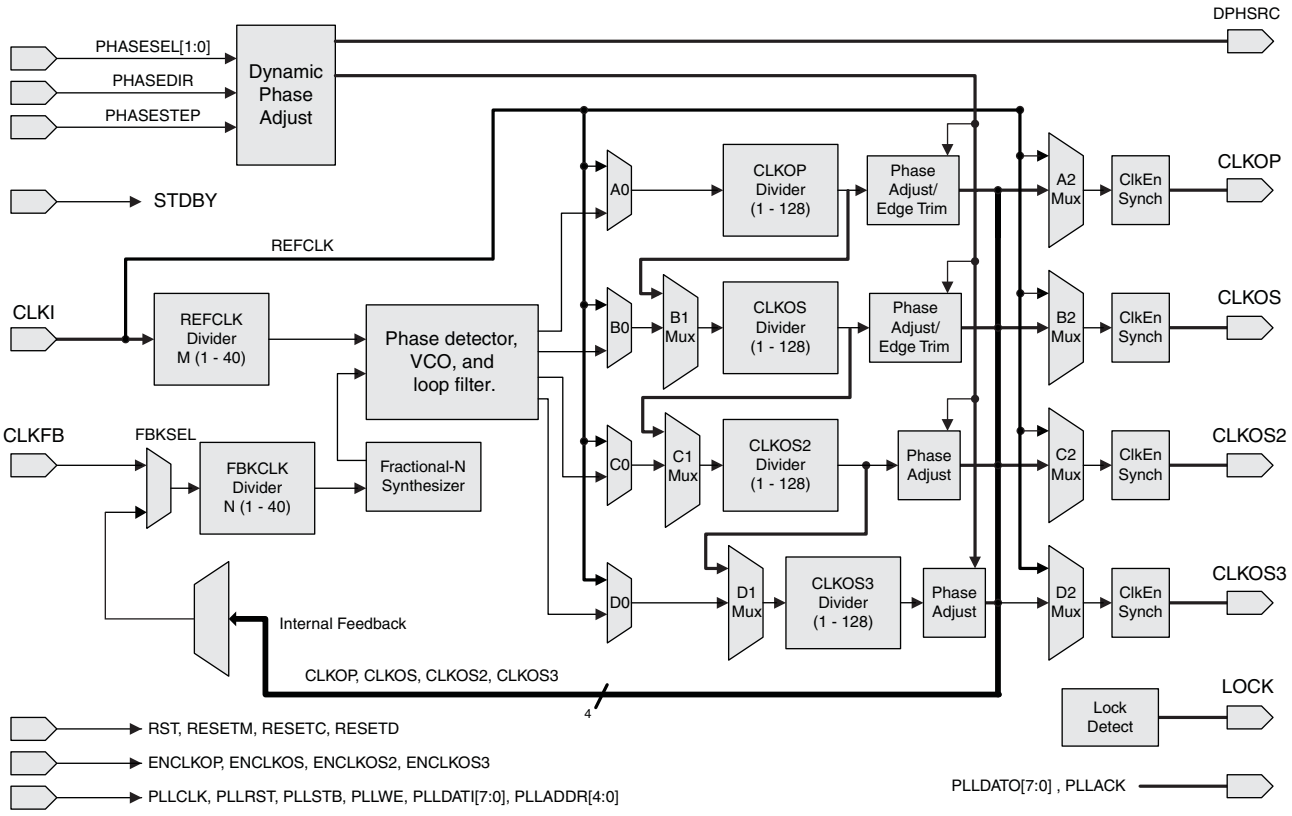


Table 2-4 provides signal descriptions of the PLL block.

Table 2-4. PLL Signal Descriptions

Port Name	I/O	Description
CLKI	I	Input clock to PLL
CLKFB	I	Feedback clock
PHASESEL[1:0]	I	Select which output is affected by Dynamic Phase adjustment ports
PHASEDIR	I	Dynamic Phase adjustment direction
PHASESTEP	I	Dynamic Phase step – toggle shifts VCO phase adjust by one step.

The EBR memory supports three forms of write behavior for single or dual port operation:

1. **Normal** – Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.

2. **Write Through** – A copy of the input data appears at the output of the same port. This mode is supported for all data widths.

3. **Read-Before-Write** – When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2^N-1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

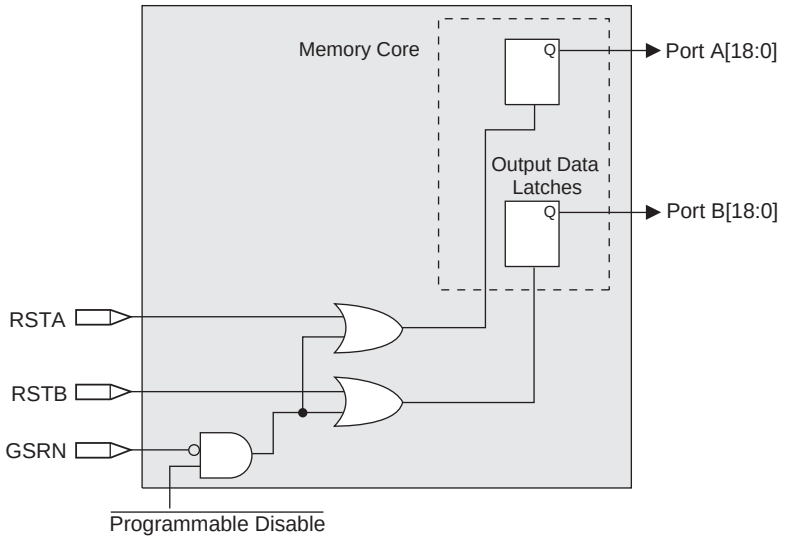
N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

Figure 2-9. Memory Core Reset

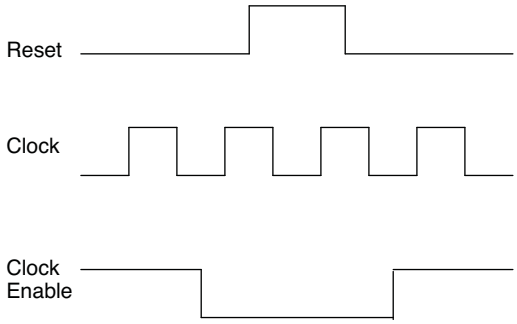


For further information on the sysMEM EBR block, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

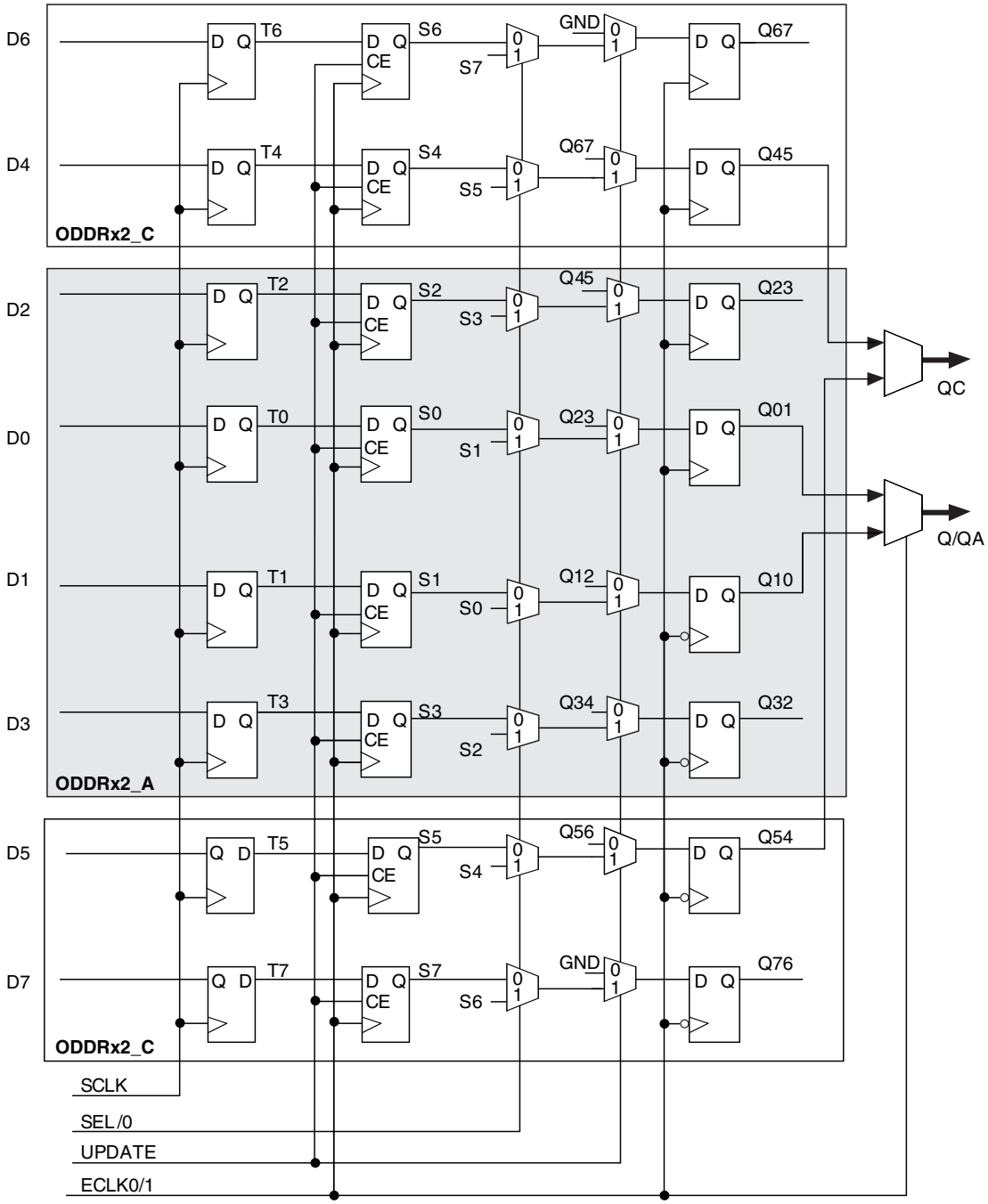
Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.

Figure 2-17. Output Gearbox



More information on the output gearbox is available in TN1203, Implementing High-Speed Interfaces with MachXO2 Devices.

Table 2-11. I/O Support Device by Device

	MachXO2-256, MachXO2-640	MachXO2-640U, MachXO2-1200	MachXO2-1200U MachXO2-2000/U, MachXO2-4000, MachXO2-7000
Number of I/O Banks	4	4	6
Type of Input Buffers	Single-ended (all I/O banks) Differential Receivers (all I/O banks)	Single-ended (all I/O banks) Differential Receivers (all I/O banks) Differential input termination (bottom side)	Single-ended (all I/O banks) Differential Receivers (all I/O banks) Differential input termination (bottom side)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O banks)	Single-ended buffers with complementary outputs (all I/O banks) Differential buffers with true LVDS outputs (50% on top side)	Single-ended buffers with complementary outputs (all I/O banks) Differential buffers with true LVDS outputs (50% on top side)
Differential Output Emulation Capability	All I/O banks	All I/O banks	All I/O banks
PCI Clamp Support	No	Clamp on bottom side only	Clamp on bottom side only

Table 2-12. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3 V**	**2.5 V**	**1.8 V**	**1.5**	**1.2 V**
Single-Ended Interfaces					
LVTTL	✓	✓[2]	✓[2]	✓[2]	
LVCMOS33	✓	✓[2]	✓[2]	✓[2]	
LVCMOS25	✓[2]	✓	✓[2]	✓[2]	
LVCMOS18	✓[2]	✓[2]	✓	✓[2]	
LVCMOS15	✓[2]	✓[2]	✓[2]	✓	✓[2]
LVCMOS12	✓[2]	✓[2]	✓[2]	✓[2]	✓
PCI[1]	✓				
SSTL18 (Class I, Class II)	✓	✓	✓		
SSTL25 (Class I, Class II)	✓	✓			
HSTL18 (Class I, Class II)	✓	✓	✓		
Differential Interfaces					
LVDS	✓	✓			
BLVDS, MVDS, LVPECL, RSDS	✓	✓			
MIPI[3]	✓	✓			
Differential SSTL18 Class I, II	✓	✓	✓		
Differential SSTL25 Class I, II	✓	✓			
Differential HSTL18 Class I, II	✓	✓	✓		

1. Bottom banks of MachXO2-640U, MachXO2-1200/U and higher density devices only.
2. Reduced functionality. Refer to TN1202, MachXO2 sysIO Usage Guide for more detail.
3. These interfaces can be emulated with external resistors in all devices.

For more details on these embedded functions, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I^2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC}.

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I^2C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

MachXO2 Family Data Sheet DC and Switching Characteristics

March 2017 Data Sheet DS1035

Absolute Maximum Ratings[1, 2, 3]

	MachXO2 ZE/HE (1.2 V)	MachXO2 HC (2.5 V / 3.3 V)
Supply Voltage V_{CC}	–0.5 V to 1.32 V	–0.5 V to 3.75 V
Output Supply Voltage V_{CCIO}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
I/O Tri-state Voltage Applied[4, 5]	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Dedicated Input Voltage Applied[4]	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature (T_J)	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of –2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.
5. The dual function I^2C pins SCL and SDA are limited to –0.25 V to 3.75 V or to –0.3 V with a duration of <20 ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}[1]	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
	Core Supply Voltage for 2.5 V / 3.3 V Devices	2.375	3.6	V
V_{CCIO}[1, 2, 3]	I/O Driver Supply Voltage	1.14	3.6	V
t_{JCOM}	Junction Temperature Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature Industrial Operation	–40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both the same voltage, they must also be the same supply.
2. See recommended voltages by I/O standard in subsequent table.
3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

Power Supply Ramp Rates[1]

Symbol	Parameter	Min.	Typ.	Max.	Units
t_{RAMP}	Power supply ramp rates for all power supplies.	0.01	—	100	V/ms

1. Assumes monotonic ramp rates.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} –0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} –0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < V_{IN} < V_{CCIO}	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	-309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < V_{IN} < V_{CCIO}	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pF
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pF
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-to-low transition. For true LVDS output pins in MachXO2-640U, MachXO2-1200/U and larger devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1202, MachXO2 sysIO Usage Guide.

sysIO Recommended Operating Conditions

Standard	V_{CCIO} (V)			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS 3.3	3.135	3.3	3.6	—	—	—
LVCMOS 2.5	2.375	2.5	2.625	—	—	—
LVCMOS 1.8	1.71	1.8	1.89	—	—	—
LVCMOS 1.5	1.425	1.5	1.575	—	—	—
LVCMOS 1.2	1.14	1.2	1.26	—	—	—
LVTTL	3.135	3.3	3.6	—	—	—
PCI[3]	3.135	3.3	3.6	—	—	—
SSTL25	2.375	2.5	2.625	1.15	1.25	1.35
SSTL18	1.71	1.8	1.89	0.833	0.9	0.969
HSTL18	1.71	1.8	1.89	0.816	0.9	1.08
LVCMOS25R33	3.135	3.3	3.6	1.1	1.25	1.4
LVCMOS18R33	3.135	3.3	3.6	0.75	0.9	1.05
LVCMOS18R25	2.375	2.5	2.625	0.75	0.9	1.05
LVCMOS15R33	3.135	3.3	3.6	0.6	0.75	0.9
LVCMOS15R25	2.375	2.5	2.625	0.6	0.75	0.9
LVCMOS12R33[4]	3.135	3.3	3.6	0.45	0.6	0.75
LVCMOS12R25[4]	2.375	2.5	2.625	0.45	0.6	0.75
LVCMOS10R33[4]	3.135	3.3	3.6	0.35	0.5	0.65
LVCMOS10R25[4]	2.375	2.5	2.625	0.35	0.5	0.65
LVDS25[1, 2]	2.375	2.5	2.625	—	—	—
LVDS33[1, 2]	3.135	3.3	3.6	—	—	—
LVPECL[1]	3.135	3.3	3.6	—	—	—
BLVDS[1]	2.375	2.5	2.625	—	—	—
RSDS[1]	2.375	2.5	2.625	—	—	—
SSTL18D	1.71	1.8	1.89	—	—	—
SSTL25D	2.375	2.5	2.625	—	—	—
HSTL18D	1.71	1.8	1.89	—	—	—

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.
2. MachXO2-640U, MachXO2-1200/U and larger devices have dedicated LVDS buffers.
3. Input on the bottom bank of the MachXO2-640U, MachXO2-1200/U and larger devices only.
4. Supported only for inputs and BIDIs for all ZE devices, and –6 speed grade for HE and HC devices.

BLVDS

The MachXO2 family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

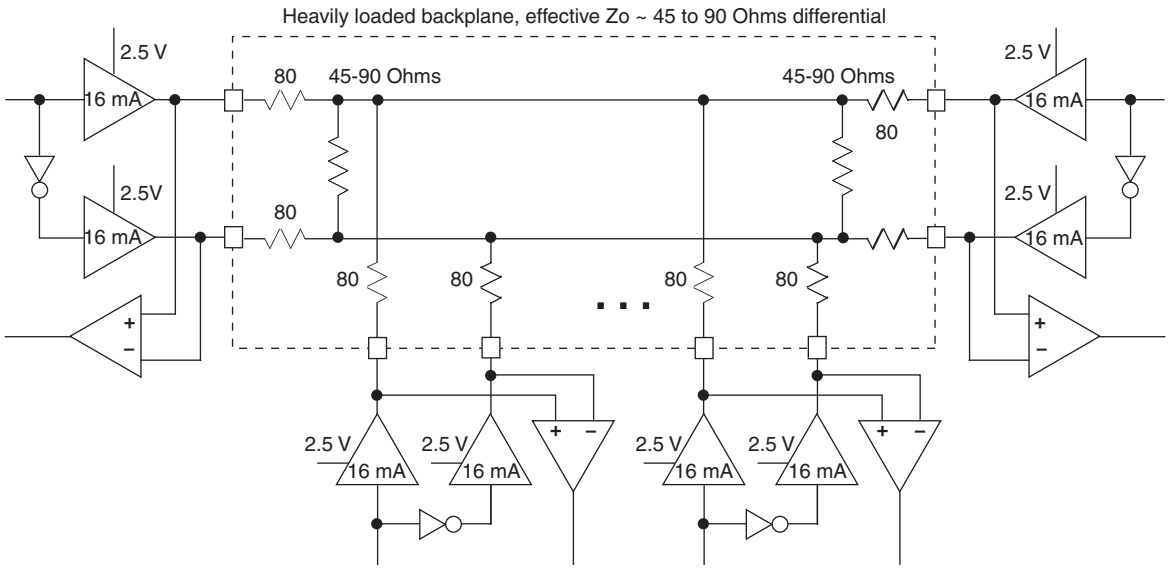


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z_{OUT}	Output impedance	20	20	Ohms
R_S	Driver series resistance	80	80	Ohms
R_{TLEFT}	Left end termination	45	90	Ohms
R_{TRIGHT}	Right end termination	45	90	Ohms
V_{OH}	Output high voltage	1.376	1.480	V
V_{OL}	Output low voltage	1.124	1.020	V
V_{OD}	Output differential voltage	0.253	0.459	V
V_{CM}	Output common mode voltage	1.250	1.250	V
I_{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Aligned[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only.[11]	—	0.290	—	0.320	—	0.345	UI
t_{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	0.703	—	UI
f_{DATA}	DDRX4 Serial Input Data Speed		—	756	—	630	—	524	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	378	—	315	—	262	MHz
f_{SCLK}	SCLK Frequency		—	95	—	79	—	66	MHz
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only.[11]	0.233	—	0.219	—	0.198	—	ns
t_{HO}	Input Data Hold After ECLK		0.287	—	0.287	—	0.344	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	756	—	630	—	524	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	378	—	315	—	262	MHz
f_{SCLK}	SCLK Frequency		—	95	—	79	—	66	MHz
7:1 LVDS Inputs (GDDR71_RX.ECLK.7:1)[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only.[11]	—	0.290	—	0.320	—	0.345	UI
t_{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	0.703	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	756	—	630	—	524	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	378	—	315	—	262	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	—	75	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides.	—	0.520	—	0.550	—	0.580	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.520	—	0.550	—	0.580	ns
f_{DATA}	DDRX1 Output Data Speed		—	300	—	250	—	208	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	150	—	125	—	104	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides.	1.210	—	1.510	—	1.870	—	ns
t_{DVA}	Output Data Valid After CLK Output		1.210	—	1.510	—	1.870	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	300	—	250	—	208	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	150	—	125	—	104	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only.	—	0.200	—	0.215	—	0.230	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.200	—	0.215	—	0.230	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	664	—	554	—	462	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	332	—	277	—	231	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	—	116	MHz

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.349	—	0.381	—	0.396	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.630	—	0.613	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	120	—	110	—	96	Mbps
f_{SCLK}	SCLK Frequency		—	60	—	55	—	48	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.347	—	0.374	—	0.393	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.637	—	0.616	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.372	—	0.394	—	0.410	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.690	—	0.658	—	0.618	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\ ns)/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 167 ps (–3), 182 ps (–2), 195 ps (–1).
8. This number for general purpose usage. Duty cycle tolerance is +/–10%.
9. Duty cycle is +/– 5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Figure 3-9. GDDR71 Video Timing Waveforms

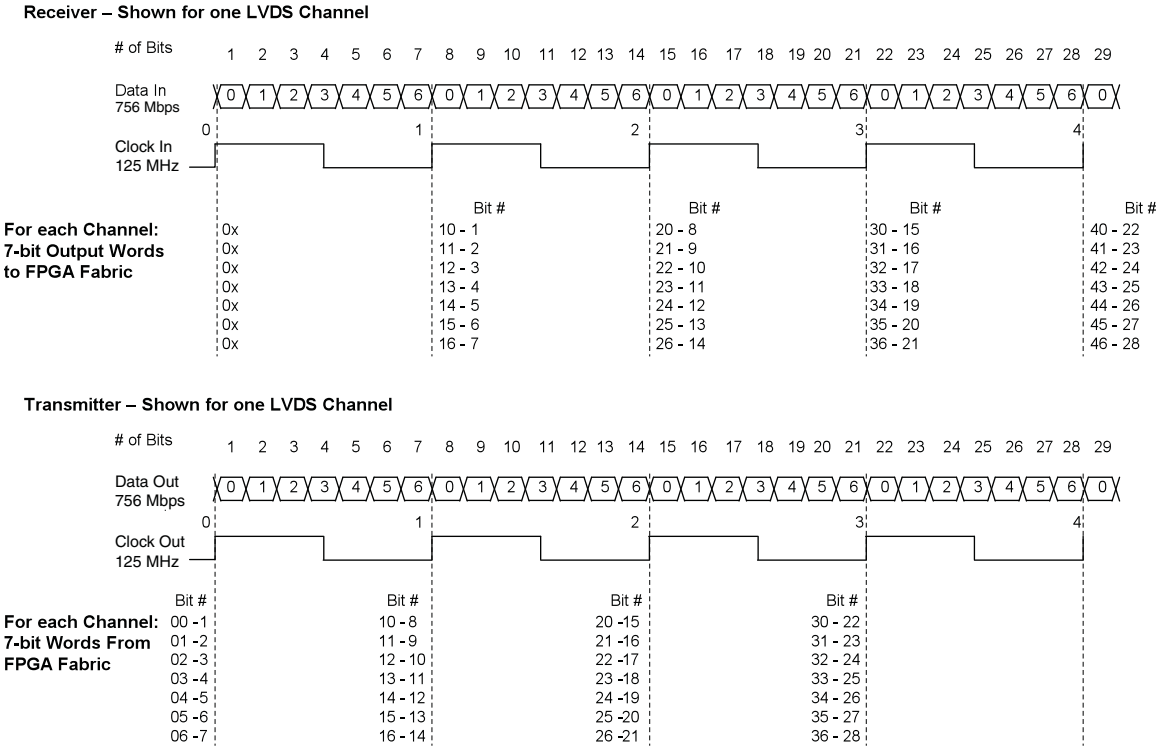


Figure 3-10. Receiver GDDR71_RX. Waveforms

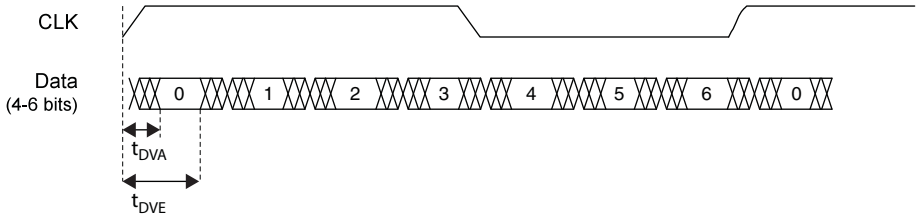
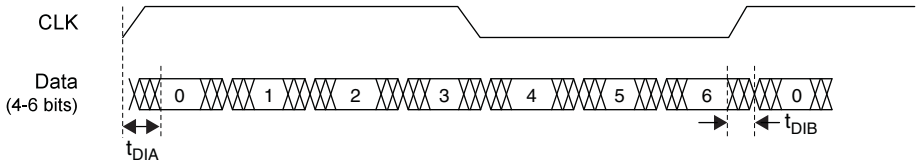


Figure 3-11. Transmitter GDDR71_TX. Waveforms



	MachXO2-2000						MachXO2-2000U
	49 WLCSP	100 TQFP	132 csBGA	144 TQFP	256 caBGA	256 ftBGA	484 ftBGA
General Purpose I/O per Bank							
Bank 0	19	18	25	27	50	50	70
Bank 1	0	21	26	28	52	52	68
Bank 2	13	20	28	28	52	52	72
Bank 3	0	6	7	8	16	16	24
Bank 4	0	6	8	10	16	16	16
Bank 5	6	8	10	10	20	20	28
Total General Purpose Single-Ended I/O	38	79	104	111	206	206	278
Differential I/O per Bank							
Bank 0	7	9	13	14	25	25	35
Bank 1	0	10	13	14	26	26	34
Bank 2	6	10	14	14	26	26	36
Bank 3	0	3	3	4	8	8	12
Bank 4	0	3	4	5	8	8	8
Bank 5	3	4	5	5	10	10	14
Total General Purpose Differential I/O	16	39	52	56	103	103	139
Dual Function I/O	24	31	33	33	33	33	37
High-speed Differential I/O							
Bank 0	5	4	8	9	14	14	18
Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	4	8	9	14	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	10	14	14	14	14	18
DQS Groups							
Bank 1	0	1	2	2	2	2	2
VCCIO Pins							
Bank 0	2	2	3	3	4	4	10
Bank 1	0	2	3	3	4	4	10
Bank 2	1	2	3	3	4	4	10
Bank 3	0	1	1	1	1	1	3
Bank 4	0	1	1	1	2	2	4
Bank 5	1	1	1	1	1	1	3
VCC	2	2	4	4	8	8	12
GND	4	8	10	12	24	24	48
NC	0	1	1	4	1	1	105
Reserved for Configuration	1	1	1	1	v	1	1
Total Count of Bonded Pins	39	100	132	144	256	256	484

	MachXO2-4000							
	84 QFN	132 csBGA	144 TQFP	184 csBGA	256 caBGA	256 ftBGA	332 caBGA	484 fpBGA
General Purpose I/O per Bank								
Bank 0	27	25	27	37	50	50	68	70
Bank 1	10	26	29	37	52	52	68	68
Bank 2	22	28	29	39	52	52	70	72
Bank 3	0	7	9	10	16	16	24	24
Bank 4	9	8	10	12	16	16	16	16
Bank 5	0	10	10	15	20	20	28	28
Total General Purpose Single Ended I/O	68	104	114	150	206	206	274	278
Differential I/O per Bank								
Bank 0	13	13	14	18	25	25	34	35
Bank 1	4	13	14	18	26	26	34	34
Bank 2	11	14	14	19	26	26	35	36
Bank 3	0	3	4	4	8	8	12	12
Bank 4	4	4	5	6	8	8	8	8
Bank 5	0	5	5	7	10	10	14	14
Total General Purpose Differential I/O	32	52	56	72	103	103	137	139
Dual Function I/O	28	37	37	37	37	37	37	37
High-speed Differential I/O								
Bank 0	8	8	9	8	18	18	18	18
Gearboxes								
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	8	8	9	9	18	18	18	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	11	14	14	12	18	18	18	18
DQS Groups								
Bank 1	1	2	2	2	2	2	2	2
VCCIO Pins								
Bank 0	3	3	3	3	4	4	4	10
Bank 1	1	3	3	3	4	4	4	10
Bank 2	2	3	3	3	4	4	4	10
Bank 3	1	1	1	1	1	1	2	3
Bank 4	1	1	1	1	2	2	1	4
Bank 5	1	1	1	1	1	1	2	3
VCC	4	4	4	4	8	8	8	12
GND	4	10	12	16	24	24	27	48
NC	1	1	1	1	1	1	5	105
Reserved for configuration	1	1	1	1	1	1	1	1
Total Count of Bonded Pins	84	132	144	184	256	256	332	484

High-Performance Commercial Grade Devices with Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256HC-4SG32C	256	2.5 V / 3.3 V	–4	Halogen-Free QFN	32	COM
LCMXO2-256HC-5SG32C	256	2.5 V / 3.3 V	–5	Halogen-Free QFN	32	COM
LCMXO2-256HC-6SG32C	256	2.5 V / 3.3 V	–6	Halogen-Free QFN	32	COM
LCMXO2-256HC-4SG48C	256	2.5 V / 3.3 V	–4	Halogen-Free QFN	48	COM
LCMXO2-256HC-5SG48C	256	2.5 V / 3.3 V	–5	Halogen-Free QFN	48	COM
LCMXO2-256HC-6SG48C	256	2.5 V / 3.3 V	–6	Halogen-Free QFN	48	COM
LCMXO2-256HC-4UMG64C	256	2.5 V / 3.3 V	–4	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-5UMG64C	256	2.5 V / 3.3 V	–5	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-6UMG64C	256	2.5 V / 3.3 V	–6	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-4TG100C	256	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-256HC-5TG100C	256	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-256HC-6TG100C	256	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-256HC-4MG132C	256	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-256HC-5MG132C	256	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-256HC-6MG132C	256	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640HC-4SG48C	640	2.5 V / 3.3 V	–4	Halogen-Free QFN	48	COM
LCMXO2-640HC-5SG48C	640	2.5 V / 3.3 V	–5	Halogen-Free QFN	48	COM
LCMXO2-640HC-6SG48C	640	2.5 V / 3.3 V	–6	Halogen-Free QFN	48	COM
LCMXO2-640HC-4TG100C	640	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-640HC-5TG100C	640	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-640HC-6TG100C	640	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-640HC-4MG132C	640	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-640HC-5MG132C	640	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-640HC-6MG132C	640	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640UHC-4TG144C	640	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-640UHC-5TG144C	640	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-640UHC-6TG144C	640	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-6BG332C	4320	1.2 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-4000HE-4FG484C	4320	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HE-5FG484C	4320	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HE-6FG484C	4320	1.2 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HE-4TG144C	6864	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-5TG144C	6864	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-6TG144C	6864	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-4BG256C	6864	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-5BG256C	6864	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-6BG256C	6864	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-4FTG256C	6864	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-5FTG256C	6864	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-6FTG256C	6864	1.2 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-4BG332C	6864	1.2 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-5BG332C	6864	1.2 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-6BG332C	6864	1.2 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-4FG484C	6864	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-7000HE-5FG484C	6864	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-7000HE-6FG484C	6864	1.2 V	–6	Halogen-Free fpBGA	484	COM

High Performance Industrial Grade Devices Without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100I	2112	1.2 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-5TG100I	2112	1.2 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-6TG100I	2112	1.2 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-4MG132I	2112	1.2 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-5MG132I	2112	1.2 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-6MG132I	2112	1.2 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-4TG144I	2112	1.2 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-5TG144I	2112	1.2 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-6TG144I	2112	1.2 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-4BG256I	2112	1.2 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-5BG256I	2112	1.2 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-6BG256I	2112	1.2 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-4FTG256I	2112	1.2 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-5FTG256I	2112	1.2 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-6FTG256I	2112	1.2 V	–6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484I	2112	1.2 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-5FG484I	2112	1.2 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-6FG484I	2112	1.2 V	–6	Halogen-Free fpBGA	484	IND